

VERSION WITH MARKINGS TO SHOW CHANGES MADE**In the claims:**

Claims 1, 4, 8, 11, 12, 15, 19, 22, 23, 26, 30 and 33 have been amended as follows:

1. (Once Amended) An electronic device comprising:
 - a semiconductor chip including an integrated circuit having at least one electrostatic discharge sensitive device; and
 - a non-semiconductor chip formed of an electrically insulating material, positioned in close proximity to said semiconductor chip, said non-semiconductor chip having at least one electrostatic discharge protection device, said electrostatic discharge protection device electrically connected to said electrostatic discharge sensitive device.

4. (Once Amended) An electronic device comprising:
 - a semiconductor chip including an integrated circuit; and
 - a non-semiconductor chip formed of an electrically insulating material, positioned in close proximity to said semiconductor chip, said non-semiconductor chip having at least one electrostatic discharge sensitive device and at least one electrostatic discharge protection device, said electrostatic discharge protection device electrically connected to said electrostatic discharge sensitive device.

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8. (Once Amended) An electronic device comprising:

a semiconductor chip including an integrated circuit having at least one first electrostatic discharge sensitive device; and

a non-semiconductor chip formed of an electrically insulating material, positioned in close proximity to said semiconductor chip, said non-semiconductor chip having at least one second electrostatic discharge sensitive device and at least one first electrostatic discharge protection device and at least one second electrostatic discharge protection device, said first electrostatic discharge protection device electrically connected to said first electrostatic discharge sensitive device and said second electrostatic discharge protection device electrically connected to said second electrostatic discharge sensitive device.

11. (Once Amended) The electronic device of claim 8, wherein:

said first electrostatic discharge sensitive device is selected from the group consisting of transistors, diodes, resistors, capacitors, and inductors;

said first electrostatic discharge protection devices is selected from the group consisting of spark gaps, field emission devices, diodes and gated diodes;

said second electrostatic discharge sensitive device is selected from the group consisting of capacitors, resistors and inductors;

said second electrostatic discharge protection device is a spark gap or a field emission device; and

said spark gap, or field emission device, and at least a portion of said second electrostatic discharge sensitive device and are integrally formed.

12. (Once Amended) An electronic device comprising:

a dual chip stack comprising:

a semiconductor chip including an integrated circuit having at least one electrostatic discharge sensitive device; and

a non-semiconductor chip formed of an electrically insulating material, attached to said semiconductor chip, said non-semiconductor chip having at least one electrostatic discharge protection device, said electrostatic discharge protection device electrically connected to said electrostatic discharge sensitive device.

15. (Once Amended) An electronic device comprising:

a dual chip stack comprising:

a semiconductor chip including an integrated circuit; and

a non-semiconductor chip formed of an electrically insulating material, attached to said semiconductor chip, said non-semiconductor chip having at least one electrostatic discharge sensitive device and at least one electrostatic discharge protection device, said electrostatic discharge protection device electrically connected to said electrostatic discharge sensitive device.

19. (Once Amended) An electronic device comprising:
a dual chip stack comprising:
a semiconductor chip including an integrated circuit having at least one first electrostatic discharge sensitive device; and
a non-semiconductor chip formed of an electrically insulating material, positioned in close proximity to said semiconductor chip, said non-semiconductor chip having at least one second electrostatic discharge sensitive device and at least one first electrostatic discharge protection device and at least one second electrostatic discharge protection device, said first electrostatic discharge protection device electrically connected to said first electrostatic discharge sensitive device and said second electrostatic discharge protection device electrically connected to said second electrostatic discharge sensitive device.
22. (Once Amended) The electronic device of claim 19, wherein:
said first electrostatic discharge sensitive device is selected from the group consisting of transistors, diodes, resistors, capacitors, and inductors;
said first electrostatic discharge protection devices is selected from the group consisting of spark gaps, field emission devices, diodes and gated diodes;
said second electrostatic discharge sensitive device is selected from the group consisting of capacitors, resistors and inductors;
said second electrostatic discharge protection device is a spark gap or a field emission device; and
said spark gap, or field emission device, and at least a portion of said second electrostatic discharge sensitive device ~~and~~ are integrally formed.

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23. (Once Amended) An electronic device comprising:

a dual chip stack mounted on a module, said dual chip stack comprising:

a semiconductor chip including an integrated circuit having at least one electrostatic discharge sensitive device; and

a non-semiconductor chip formed of an electrically insulating material, attached to said semiconductor chip, said non-semiconductor chip having at least one electrostatic discharge protection device, said electrostatic discharge protection device electrically connected to said electrostatic discharge sensitive device.

26. (Once Amended) An electronic device comprising:

a dual chip stack mounted on a module, said dual chip stack comprising:

a semiconductor chip including an integrated circuit; and

a non-semiconductor chip formed of an electrically insulating material, attached to said semiconductor chip, said non-semiconductor chip having at least one electrostatic discharge sensitive device and at least one electrostatic discharge protection device, said electrostatic discharge protection device electrically connected to said electrostatic discharge sensitive device.

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30. (Once Amended) An electronic device comprising:
a dual chip stack mounted on a module, said dual chip stack comprising:
a semiconductor chip including an integrated circuit having at least one first electrostatic discharge sensitive device; and
a non-semiconductor chip formed of an electrically insulating material, positioned in close proximity to said semiconductor chip, said non-semiconductor chip having at least one second electrostatic discharge sensitive device and at least one first electrostatic discharge protection device and at least one second electrostatic discharge protection device, said first electrostatic discharge protection device electrically connected to said first electrostatic discharge sensitive device and said second electrostatic discharge protection device electrically connected to said second electrostatic discharge sensitive device.
33. (Once Amended) The electronic device of claim 30, wherein:
said first electrostatic discharge sensitive device is selected from the group consisting of transistors, diodes, resistors, capacitors, and inductors;
said first electrostatic discharge protection devices is selected from the group consisting of spark gaps, field emission devices, diodes and gated diodes;
said second electrostatic discharge sensitive device is selected from the group consisting of capacitors, resistors and inductors;
said second electrostatic discharge protection device is a spark gap or a field emission device; and
said spark gap, or field emission device, and at least a portion of said second electrostatic discharge sensitive device ~~and~~ are integrally formed.

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